Sir:

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Transmitted herewith for filing is the Patent Application of:

Inventor: MIN-HSIUNG CHIANG, JIN-YUAN LEE AND JENN MING HUANG

For: METHOD FOR FORMING HIGH PURITY SILICON OXIDE FIELD OXIDE ISOLATION REGION

JC586 U.S. PTO

Enclosed are:

06/04/99

 \mathbf{x} <u>1</u> sheets of drawing(s) - formal.

An assignment of the invention to Taiwan Semiconductor Manufacturing Company

An associate power of attorney

The filing fee has been calculated as shown below:

	(Col. 1) (Col. 2) (OTHER THAN A	SMALL ENTITY	
FOR:	NO. FILED	NO. EXTRA	RATE	FEE	
BASIC FEE				\$ 760.	
TOTAL CLAIMS	10 - 20=	00	x 18 =	\$ 0.	
INDEP CLAIMS	2 -3=	0	x 78 =	\$ 0.	
MULTIPLE	DEPENDENT CLA	IM PRESENTED	+ 260 =		
Unit Unit		s	UB_TOTAL	\$ 760.	
		A	SSIGNMENT	\$40.	
		LT	OTAL	\$ 800.	

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X Any additional filing fees required under 37 CFR \$1.16.

X Any patent application processing fees under 37 CFR §1.17.

Respectfully submitted,

STEPHEN B. ACKERMAN, REG. NO. 37,761

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SEI	RIAL NUMBER		FILING DATE	CLASS	GRO	OUP ART UNIT	ATTORNEY DO	CKET NO.			
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¥	MIN-HSIUNG CHIANG, TAIPEI, TAIWAN; JIN-YUAN LEE, HSIN-CHU, TAIWAN; JENN-MING HUANG, HSIN-CHU, TAIWAN.										
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	METHOD FOR FORMING HIGH PURITY SILICON OXIDE FIELD OXIDE ISOLATION REGION										
FN RE	ING FEE CEIVED \$760	No	ority has been giv _ to charge/credi for the	t DEPOSIT	ACCOUNT	1.17 Fee	es (Filing) es (Processing es (Issue)	Ext. of tim)			

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